Product data sheet

1. General description

PNP low V_{CEsat} transistor, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with medium power capability and visible and soldarable side pads.

NPN complement: PBSS4360PAS

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- High temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) area requirements
- Leadless small SMD plastic package with soldarable side pads
- · Exposed heat sink for excellent thermal and electrical conductivity
- Suitable for Automatic Optical Inspection (AOI) of solder joint

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- · Charging circuits
- · Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-60	V
I _C	collector current		-	-	-3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-6	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	87	150	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	
2	Е	emitter		С
3	С	collector	Transparent top view DFN2020D-3 (SOT1061D)	B — E sym013

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5360PAS		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); no leads; 3 terminals; 1.3 mm pitch; 2 mm x 2 mm x 0.65 mm body	<u>SOT1061D</u>			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5360PAS	EA

60 V, 3 A PNP low VCEsat transistor

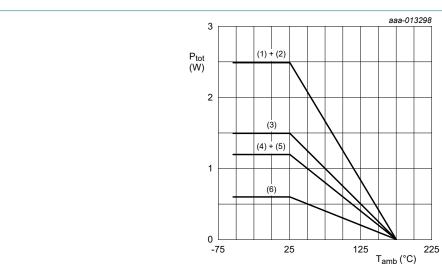
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-80	V
V_{CEO}	collector-emitter voltage	open base		-	-60	V
V_{EBO}	emitter-base voltage	open collector		-	-8	V
I _C	collector current			-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-6	Α
I _B	base current			-	-500	mA
I _{BM}	peak base current			-	-1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.6	W
			[2] [3]	-	1.2	W
			[4]	-	1.5	W
			[5] [6]	-	2.5	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm². [4]
- [5]
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, single-sided copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm²
- (3) FR4 PCB, single-sided copper, 6 cm²
- (4) FR4 PCB, single-sided copper, 1 cm²
- (5) FR4 PCB, 4-layer copper, standard footprint
- (6) FR4 PCB, single-sided copper, standard footprint

Power derating curves Fig. 1.

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistanc junction to ambie	thermal resistance from		[1]	-	-	250	K/W
	junction to ambient		[2] [3]	-	-	125	K/W
			[4]	-	-	100	K/W
			[5] [6]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm².

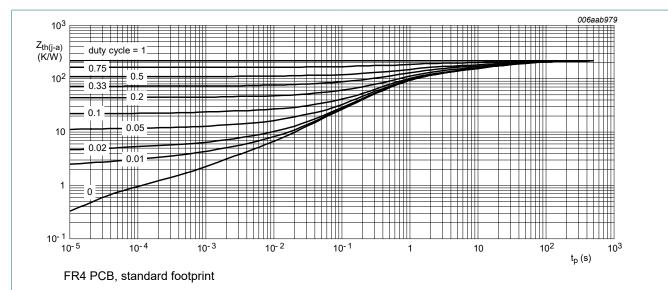


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

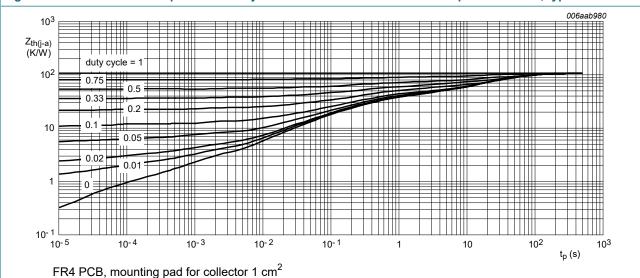


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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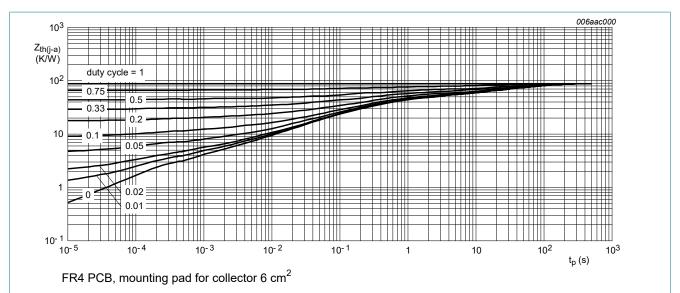
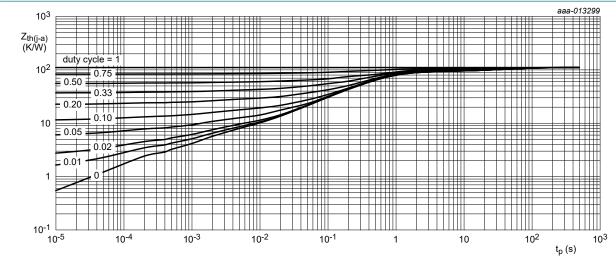


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

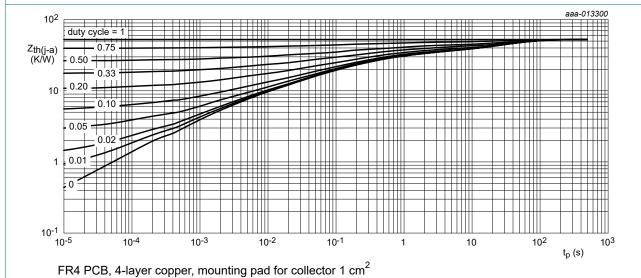
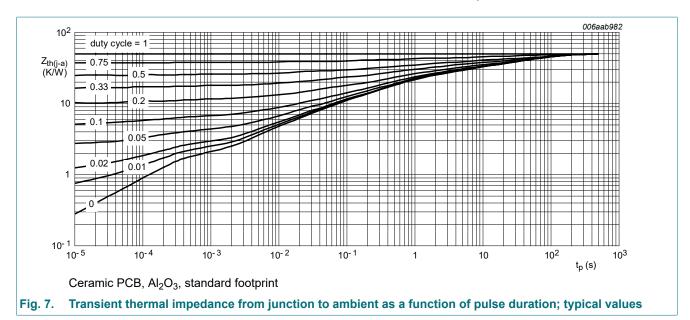


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 3 A PNP low VCEsat transistor



60 V, 3 A PNP low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -64 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -64 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -6.4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	150	250	-	
		V_{CE} = -5 V; I_C = -500 mA; pulsed; $t_p \le$	130	220	-	
		300 μs; δ ≤ 0.02; T _{amb} = 25 °C	120	200	-	
		V_{CE} = -5 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	160	-	
		V_{CE} = -5 V; I_{C} = -3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	80	125	-	
OLSat	collector-emitter saturation voltage	I_C = -0.5 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-55	-100	mV
		I_C = -1 A; I_B = -100 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-95	-170	mV
		I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-170	-320	mV
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$	-	-260	-450	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	87	150	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -2 A; I_B = -100 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.9	-1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -5 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.8	-1	V
t _d	delay time	I _C = -2 A; I _{Bon} = -0.1 A; I _{Boff} = 0.1 A;	-	12	-	ns
t _r	rise time	T _{amb} = 25 °C	-	95	-	ns
t _{on}	turn-on time		-	107	-	ns
t _s	storage time		-	160	-	ns
t _f	fall time		-	50	-	ns
t _{off}	turn-off time		-	210	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	65	120	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V; } I_E = 0 \text{ A; } i_e = 0 \text{ A; } f = 1 \text{ MHz; } T_{amb} = 25 \text{ °C}$	-	28	32	pF

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aaa-019934

28 mA

-20 mA -16 mA

-12 mA

-8 mA

-4 mA

-1.5 V_{CE} (V)

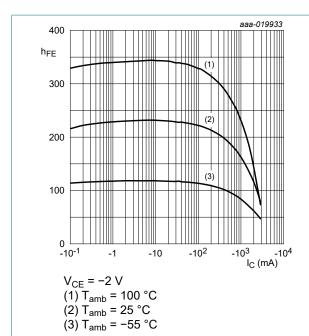
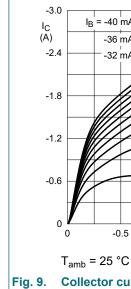


Fig. 8. DC current gain as a function of collector current; typical values



I_B = -40 mA

-36 mA

-32 mA =

-0.5

Collector current as a function of collectoremitter voltage; typical values

-1.0

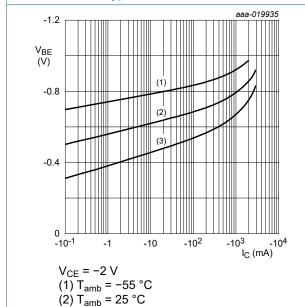
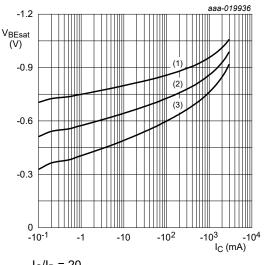


Fig. 10. Base-emitter voltage as a function of collector current; typical values

(3) $T_{amb} = 100 \, ^{\circ}C$



 $I_{\rm C}/I_{\rm B}=20$ (1) $T_{amb} = -55$ °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values

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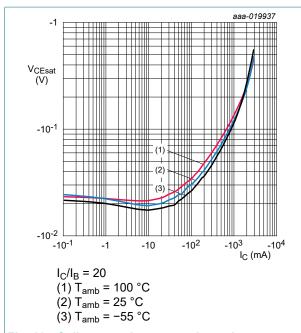


Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

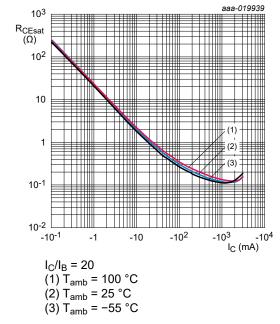


Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values

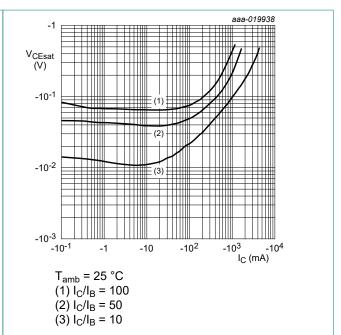


Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values

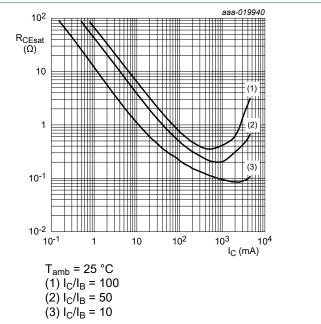


Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

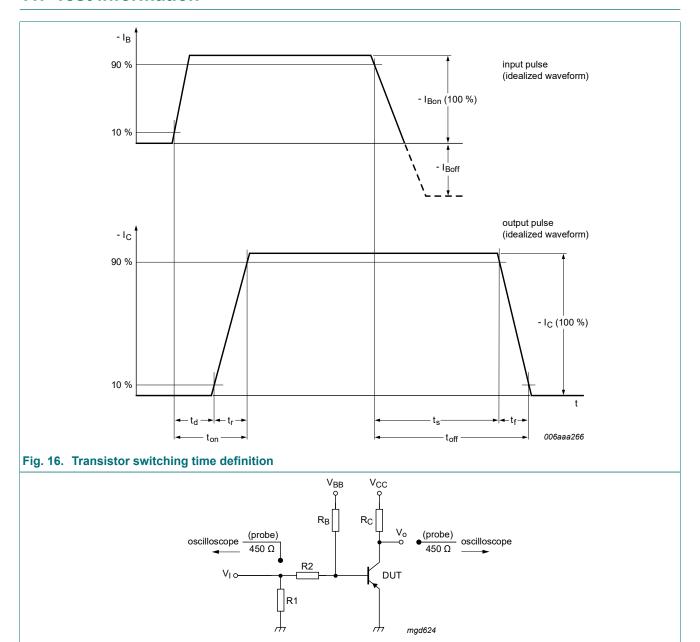
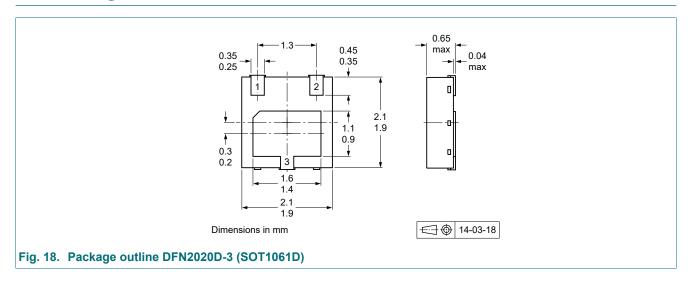


Fig. 17. Test circuit for switching times

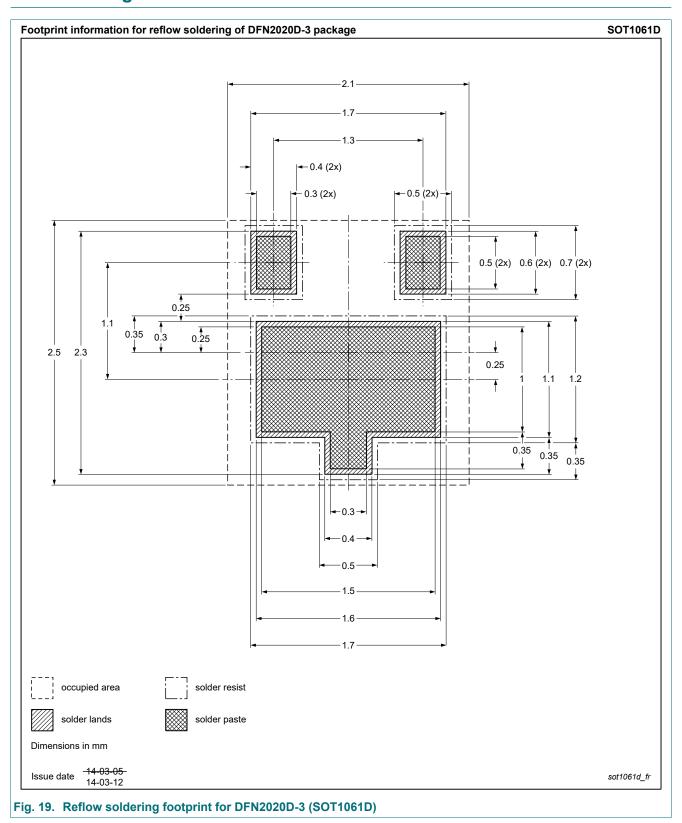
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5360PAS v.2	20230701	Product data sheet	-	PBSS5360PAS v.1		
Modifications:	 Product changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s). 					
PBSS5360PAS v.1	20151012	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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